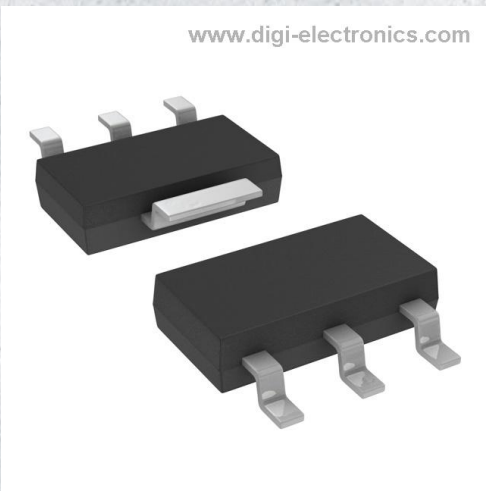
IRLM210ATF Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number	IRLM210ATF-DG
Manufacturer	onsemi
Manufacturer Product Number	IRLM210ATF
Description	MOSFET N-CH 200V 770MA SOT223-4
Detailed Description	N-Channel 200 V 770mA (Ta) 1.8W (Tc) Surface Mount SOT-223-4

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
IRLM210ATF	onsemi
Series:	Product Status:
-	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
200 V	770mA (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
5V	1.5Ohm @ 390mA, 5V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
2V @ 250µA	9 nC @ 5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	240 pF @ 25 V
FET Feature:	Power Dissipation (Max):
-	1.8W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
SOT-223-4	TO-261-4, TO-261AA
Base Product Number:	
IRLM21	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
EAR99	8541.29.0095

Advanced Power MOSFET

IRLM210A

BV_{DSS} = 200 V

$R_{DS(on)}$ = 1.5 Ω

I_D = 0.77 A

SOT-223

1. Gate 2. Drain 3. Source

FEATURES

- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current : 10 μA (Max.) @ V_{DS} = 200V
- Lower $R_{DS(ON)}$: 1.185 Ω (Typ.)

Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
V_{DSS}	Drain-to-Source Voltage	200	V
I_D	Continuous Drain Current (T_A=25°C)	0.77	A
	Continuous Drain Current (T_A=70°C)	0.62	
I_{DM}	Drain Current-Pulsed ①	6.1	A
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulsed Avalanche Energy ②	27	mJ
I_{AR}	Avalanche Current ①	0.77	A
E_{AR}	Repetitive Avalanche Energy ①	0.18	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
P_D	Total Power Dissipation (T_A=25°C) *	1.8	W
	Linear Derating Factor *	0.014	W/°C
T_J , T_{STG}	Operating Junction and Storage Temperature Range	- 55 to +150	°C
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8 " from case for 5-seconds	300	

Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient *	--	69.4	°C/W

* When mounted on the minimum pad size recommended (PCB Mount).

IRLM210A

N-CHANNEL POWER MOSFET

Electrical Characteristics (T_C=25°C unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV_{DSS}	Drain-Source Breakdown Voltage	200	--	--	V	V_{GS}=0V,I_D=250μA
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	0.19	--	V/°C	I_D=250μA ***See Fig 7***
$V_{GS(th)}$	Gate Threshold Voltage	1.0	--	2.0	V	V_{DS}=5V,I_D=250μA
I_{GSS}	Gate-Source Leakage , Forward	--	--	100	nA	V_{GS}=20V
	Gate-Source Leakage , Reverse	--	--	-100		V_{GS}=--20V
I_{DSS}	Drain-to-Source Leakage Current	--	--	10	μA	V_{DS}=200V
		--	--	100		V_{DS}=160V,T_C=125°C
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	1.5	Ω	V_{GS}=5V,I_D=0.39A ④
g_{fs}	Forward Transconductance	--	1.8	--	℧	V_{DS}=40V,I_D=0.39A ④
C_{iss}	Input Capacitance	--	185	240	pF	V_{GS}=0V,V_{DS}=25V,f =1MHz ***See Fig 5***
C_{oss}	Output Capacitance	--	35	45		
C_{rss}	Reverse Transfer Capacitance	--	14	20		
$t_{d(on)}$	Turn-On Delay Time	--	9	30	ns	V_{DD}=100V,I_D=3.3A, R_G=22Ω ***See Fig 13*** ④ ⑤
t_r	Rise Time	--	9	30		
$t_{d(off)}$	Turn-Off Delay Time	--	20	50		
t_f	Fall Time	--	6	20		
Q_g	Total Gate Charge	--	6.1	9	nC	V_{DS}=160V,V_{GS}=5V, I_D=3.3A ***See Fig 6 & Fig 12*** ④ ⑤
Q_{gs}	Gate-Source Charge	--	1.4	--		
Q_{gd}	Gate-Drain(" Miller ") Charge	--	2.8	--		

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I_S	Continuous Source Current	--	--	0.77	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current ①	--	--	6.1		
V_{SD}	Diode Forward Voltage ④	--	--	1.5	V	T_J=25°C,I_S=0.77A,V_{GS}=0V
t_{rr}	Reverse Recovery Time	--	123	--	ns	T_J=25°C,I_F=3.3A di$_F$/dt=100A/μs ④
Q_{rr}	Reverse Recovery Charge	--	0.38	--	μC	

Notes ;

① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature

② L=70mH, I_{AS}=0.77A, V_{DD}=50V, R_G=27Ω, Starting T_J=25°C

③ I_{SD}≤3.3A, di/dt≤140A/μs, V_{DD}≤BV_{DSS}, Starting T_J=25°C

④ Pulse Test : Pulse Width = 250μs, Duty Cycle ≤ 2%

⑤ Essentially Independent of Operating Temperature

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N-CHANNEL
POWER MOSFET

IRLM210A

Fig 1. Output Characteristics

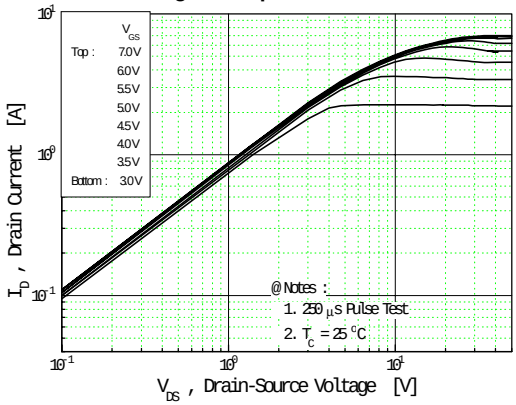

Fig 2. Transfer Characteristics

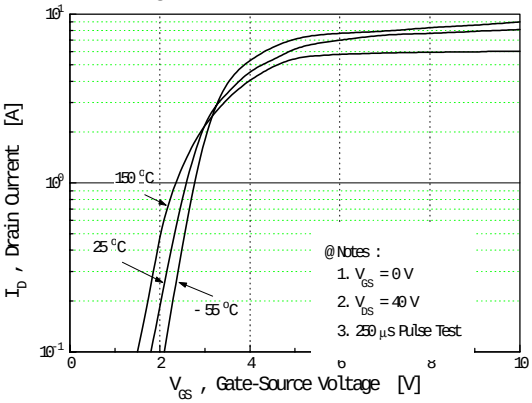

Fig 3. On-Resistance vs. Drain Current

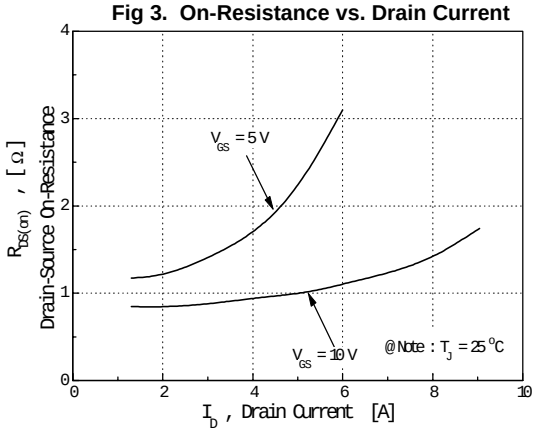

Fig 4. Source-Drain Diode Forward Voltage

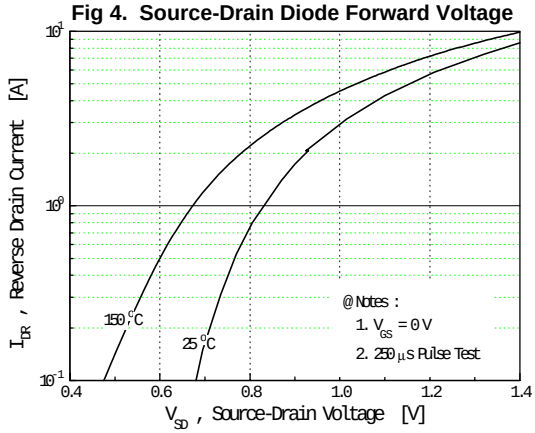

Fig 5. Capacitance vs. Drain-Source Voltage

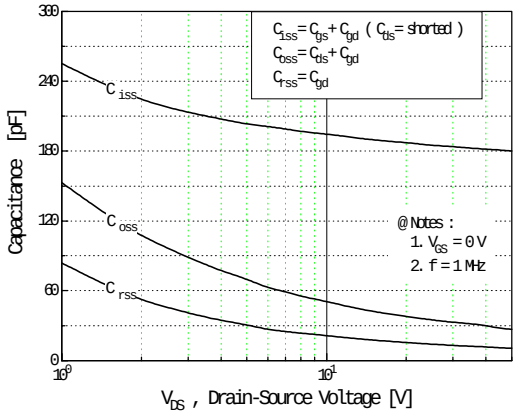

Fig 6. Gate Charge vs. Gate-Source Voltage

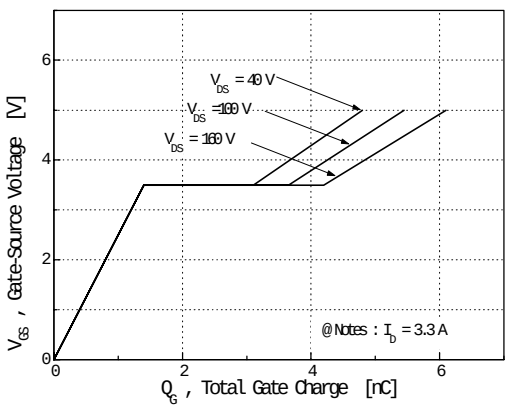

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Fig 7. Breakdown Voltage vs. Temperature

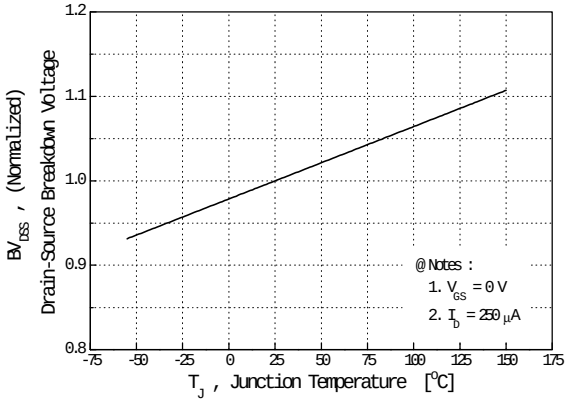

Fig 8. On-Resistance vs. Temperature

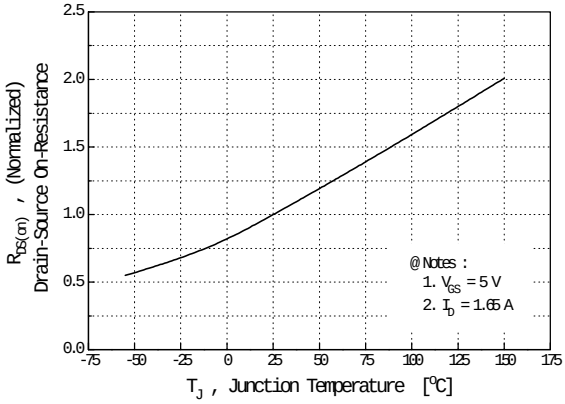

Fig 9. Max. Safe Operating Area

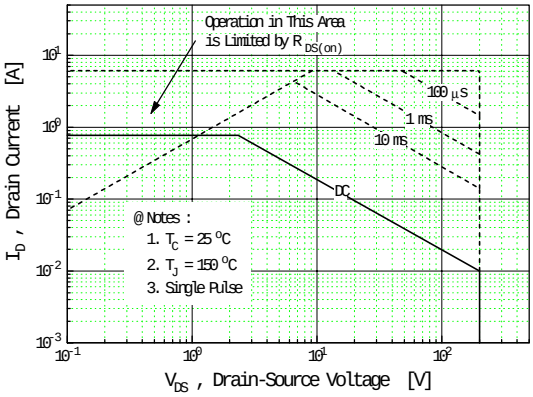

Fig 10. Max. Drain Current vs. Ambient Temperature

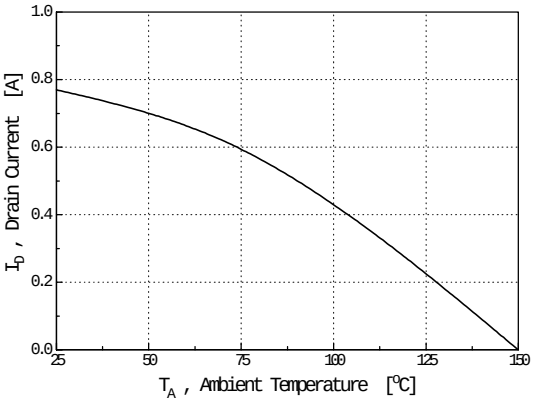

Fig 11. Thermal Response

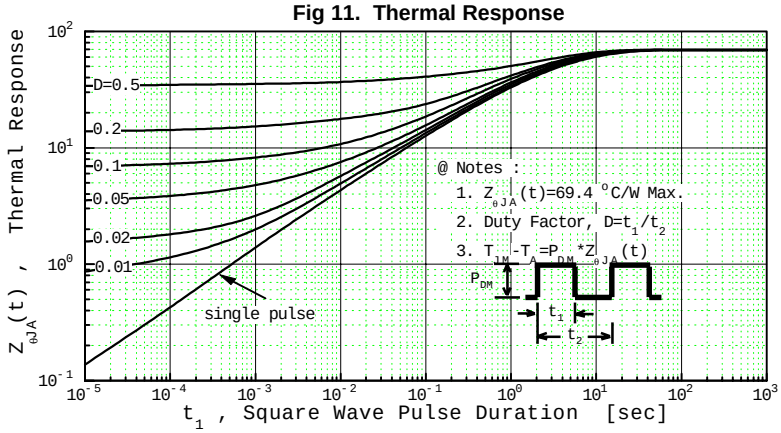

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Fig 12. Gate Charge Test Circuit & Waveform

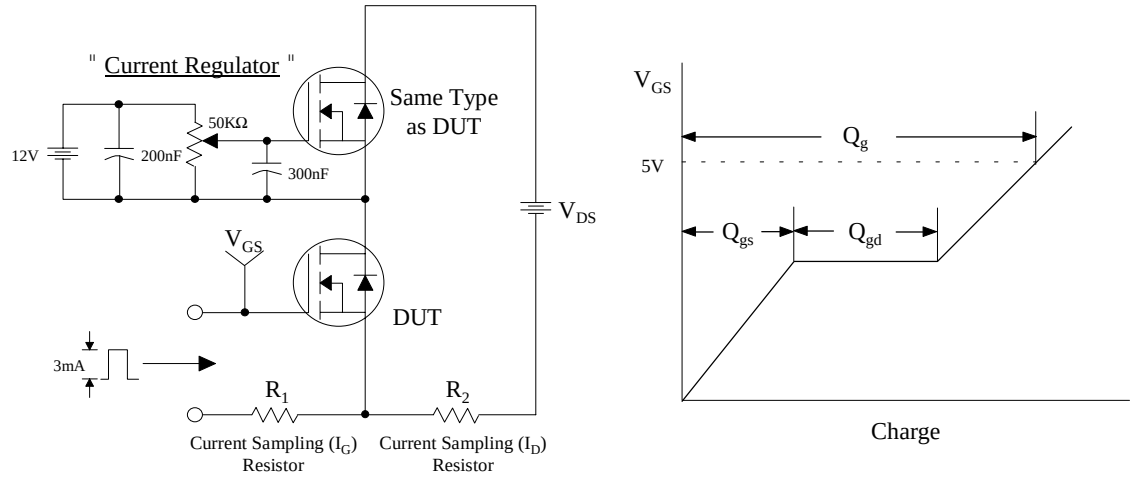


Fig 13. Resistive Switching Test Circuit & Waveforms

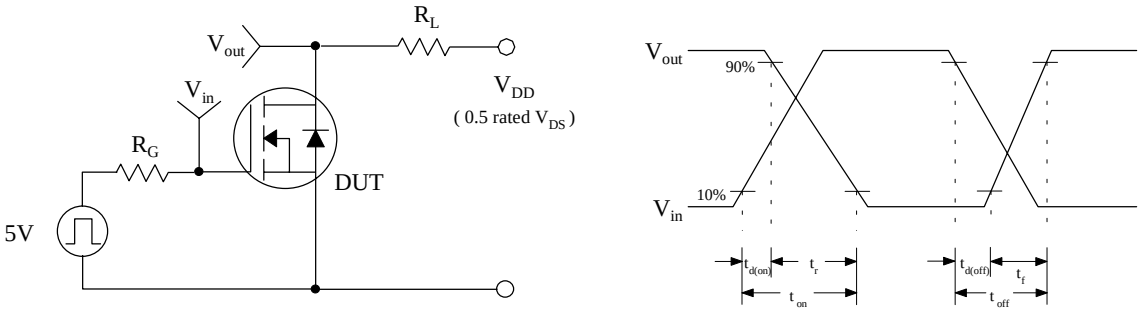


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

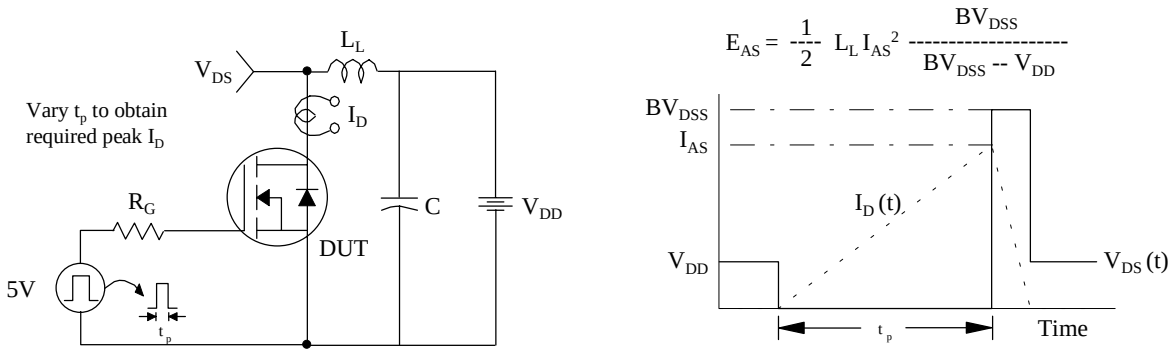
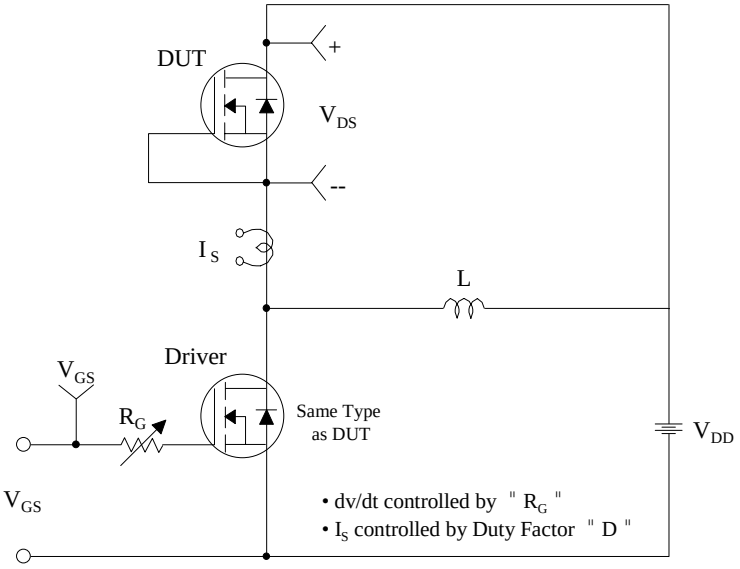
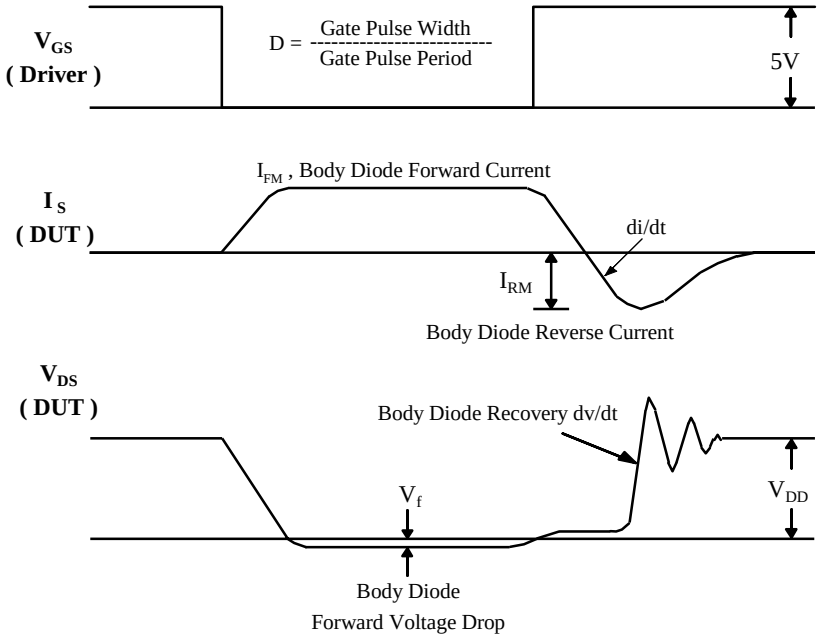


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





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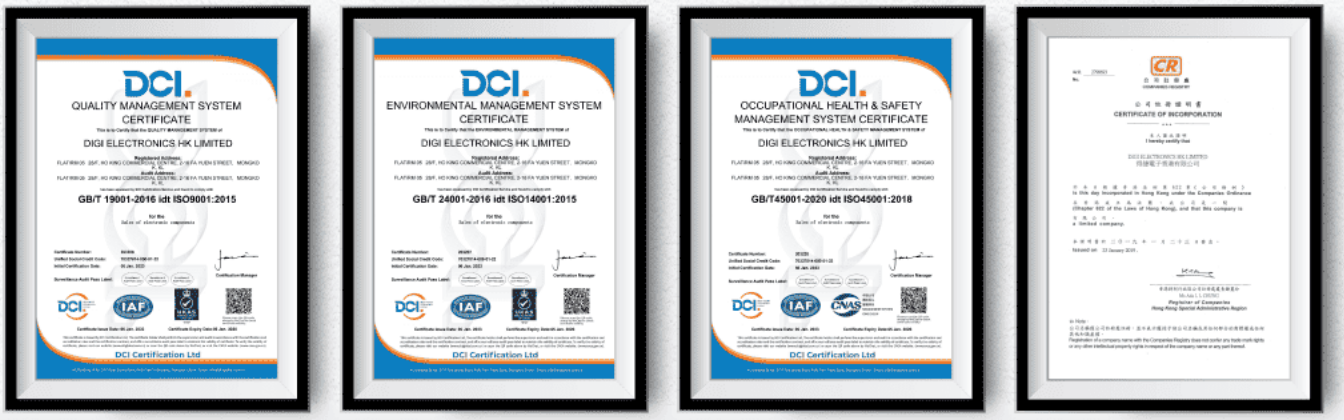

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